OXFORD INSTRUMENTS

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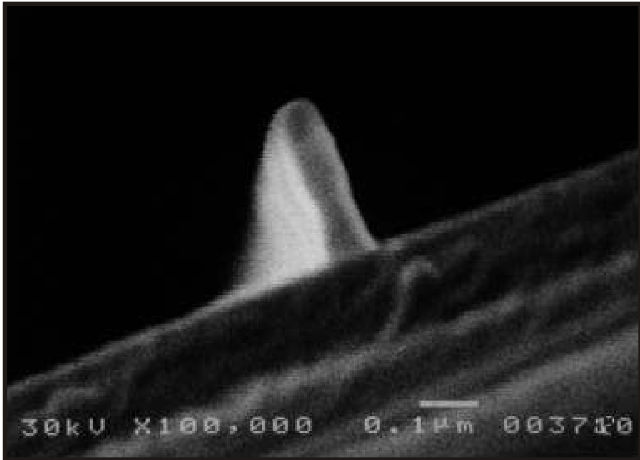
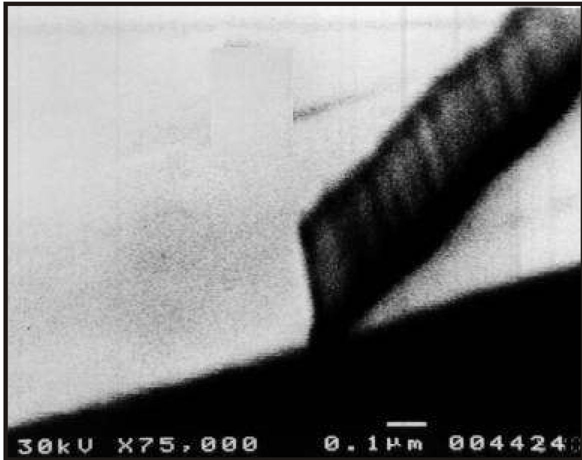
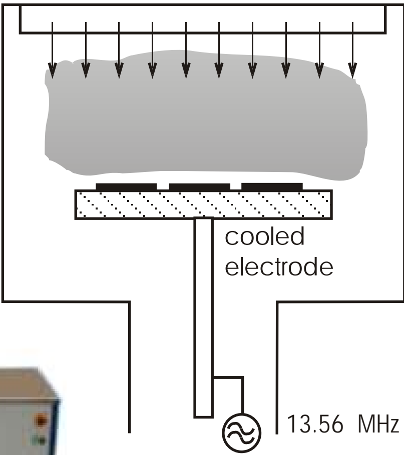
# Plasmalab Data

## *polySi RIE of 25 nm lines*



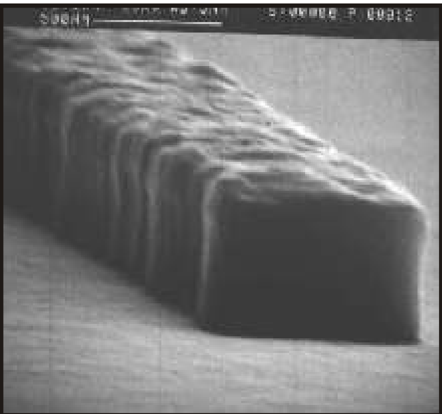



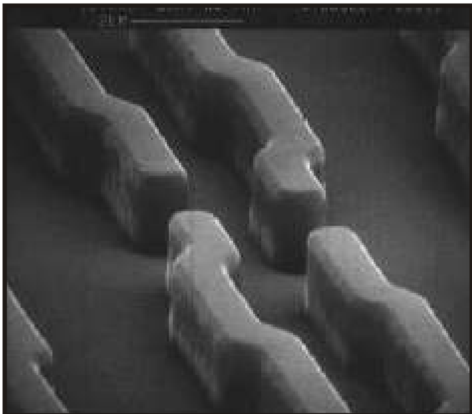

60 nm and 25 nm lines etched in polySi
(Courtesy of University of Dortmund,
Lehrstuhl für Bauelemente
der Elektrotechnik, Dr. U. Hilleringmann)




Uni Dortmund: Cl2 based process

The SEM's shows 25 nm and 60 nm lines.
rate: 50 nm/ min
selectivity to $Si_3N_4$m ask: > 30 : 1
selectivity to underlying $SiO_2$> 30 : 1
uniformity < ± 4 % (100 mm Si wafer)
excellent linewidth control





OPT application lab

HBr based process
rate: ca 100 nm/ min
uniformity: <= +/- 5 % (6")
selectivity to SiO2: > 50 : 1
anisotropic profile

*Plasmalab System 100*

*Plasmalab System 133*